

## Amendments to the Claims

This listing of claims will replace all prior versions, and listings of claims in the application.

### Listing of Claims:

1 – 22. (cancelled)

23. (currently amended): A stack of dielectric layers located over the surface of a substrate and comprising a carbon-doped SiO<sub>2</sub> dielectric layer having a first etch rate and a carbon-doped silicon nitride dielectric layer having a second etch rate, wherein the carbon-doped SiO<sub>2</sub> dielectric layer and the carbon-doped silicon nitride dielectric layer have detectably different etch characteristics but generally equal dielectric constants of less than 3, and wherein the first etch rate is greater than the second etch rate.

24. (cancelled)

25. (currently amended): A stack as claimed in Claim ~~[[24]]~~ 23 wherein a difference in the dielectric constants of the carbon-doped SiO<sub>2</sub> dielectric layer and the carbon-doped silicon nitride dielectric layer is less than 10%.

26. (currently amended): A stack of dielectric layers located over the surface of a substrate and comprising a carbon-doped SiO<sub>2</sub> dielectric layer having a first etch rate and a nitrogen-doped SiC dielectric layer having a second etch rate, wherein the carbon-doped SiO<sub>2</sub> dielectric layer and the nitrogen-doped SiC dielectric layer have detectably different etch characteristics but generally equal dielectric constants of less than 3, and wherein the first etch rate is greater than the second etch rate.

27. (cancelled)

28. (currently amended): A stack as claimed in Claim ~~[[27]]~~ 26 wherein a difference in the dielectric constants of the carbon-doped SiO<sub>2</sub> dielectric layer and the nitrogen-doped SiC dielectric layer is less than 10%.

29. (new): A stack as claimed in Claim 25 wherein the ratio of the first etch rate to the second etch rate is at least 2.5:1.

30. (new): A stack as claimed in Claim 28 wherein the ratio of the first etch rate to the second etch rate is at least 2.5:1.

31. (new): A stack as claimed in Claim 25 wherein the ratio of the first etch rate to the second etch rate is at least 2.5:1.

32. (new): A stack as claimed in Claim 28 wherein the ratio of the first etch rate to the second etch rate is at least 2.5:1.